

**AMENDMENTS TO THE CLAIMS**

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

**Listing of Claims:**

1. (Currently Amended) A method of manufacturing an epoxy resin composition for semiconductor encapsulating by use of a kneader provided with a suction hole on the downstream side of a kneading region in a conveying direction of the epoxy resin composition, and being provided with a supply orifice and a discharge orifice respectively disposed on the upstream side and the downstream side in the conveying direction of the epoxy resin composition, the method comprising:

~~the step of kneading the epoxy resin composition, while discharging a volatile~~ gas in the kneader out of the kneader through the suction hole, and simultaneously introducing outside air to the kneader through the supply orifice and the discharge orifice.

2. (Original) The method of manufacturing the epoxy resin composition for semiconductor encapsulating according to claim 1, wherein a quantity of the gas to be discharged from the kneader is in the range of 3 to 60 m<sup>3</sup>/h, and the quantity of the outside air to be introduced through the supply orifice is in the range of 0.1 to 2 m<sup>3</sup>/h.

3. (Currently Amended) An epoxy resin composition for semiconductor encapsulating manufactured by the method according to claim 1-~~or~~ 2.

4. (Original) The epoxy resin composition for semiconductor encapsulating according to claim 3, comprising an epoxy resin, a curing agent for the epoxy resin, and an inorganic filler.

5. (Original) The epoxy resin composition for semiconductor encapsulating according to claim 4, wherein the quantity of the inorganic filler to be mixed is in the range of 70 to 97 wt% based on the total weight of the composition.

6. (Currently Amended) A semiconductor device encapsulated with the epoxy resin composition for semiconductor encapsulating according to ~~any one of~~ claims claim 3 to 5.

7. (New) An epoxy resin composition for semiconductor encapsulating manufactured by the method according to claim 2.

8. (New) A semiconductor device encapsulated with the epoxy resin composition for semiconductor encapsulating according to claim 7.

9. (New) The epoxy resin composition for semiconductor encapsulating according to claim 7, comprising an epoxy resin, a curing agent for the epoxy resin, and an inorganic filler.

10. (New) The epoxy resin composition for semiconductor encapsulating according to claim 9, wherein the quantity of the inorganic filler to be mixed is in the range of 70 to 97 wt% based on the total weight of the composition.

11. (New) A semiconductor device encapsulated with the epoxy resin composition for semiconductor encapsulating according to claim 4.